

AMENDMENTS TO THE CLAIMS

This listing of claims replaces all prior versions, and listings, of claims in the application.

1. (Currently Amended) A method for burying a resist comprising:
forming an interlayer film on a substrate;
forming an opening in said interlayer film;
applying a resist film to said interlayer film, including said opening; and
patterning said resist film substantially in the same form as said opening by exposing said resist with a photomask having a light-shielding portion or a light-transmitting portion substantially in the same form as said opening and developing said resist, thereby burying said resist film inside of said opening.

2. (Currently Amended) A method for burying a resist comprising:
forming an interlayer film on a substrate;
forming an opening in said interlayer film;
forming a second film on said interlayer film including said opening;
applying a resist film to said second film; and
patterning said resist film substantially in the same form as said opening by exposing said resist with a photomask having a light-shielding portion or a light-transmitting portion substantially in the same form as said opening and developing said resist, thereby burying said resist film inside of said opening.

3. (Previously Presented) The method for burying a resist according to claim 1, wherein said resist is positive resist and including patterning said resist with a photomask having a light-shielding portion smaller in area than said opening.

4. (Previously Presented) The method for burying a resist according to claim 2, wherein said resist is a positive resist and including patterning said resist with a photomask having a light-shielding portion smaller in area than said opening.

5. (Previously Presented) The method for burying a resist according to claim 1, wherein said resist is a negative resist and including patterning said resist with a photomask having a light-transmitting portion smaller in area than said opening.

6. (Previously Presented) The method for burying a resist according to claim 2, wherein said resist is a negative resist and including patterning said resist with a photomask having a light-transmitting portion smaller in area than said opening.

7. (Currently Amended) A method for manufacturing a semiconductor device comprising:

forming an interlayer film on a substrate;

forming an opening in said interlayer film;

applying a resist film to said interlayer film, including said opening;

patterning said resist film substantially in the same form as said opening by exposing said resist with a photomask having a light-shielding portion or a light-transmitting portion substantially in the same form as said opening and developing said resist, thereby burying said resist film in said opening; and

etching said interlayer film while masking a bottom portion of said opening with said resist film buried in said opening.

8. (Currently Amended) A method for manufacturing a semiconductor device comprising:

forming an interlayer film on a substrate;

forming an opening in said interlayer film;

applying a second film on said interlayer film, including said opening;

applying a resist film on said second film; and

patterning said resist film substantially in the same form as said opening by exposing said resist with a photomask having a light-shielding portion or a light-transmitting portion substantially in the same form as said opening and developing said resist, thereby burying said resist film in said opening; and

etching said second film while masking a bottom portion of said opening with said resist film buried in said opening.